

TOSHIBA Photocoupler GaAs Ired & Photo Transistor

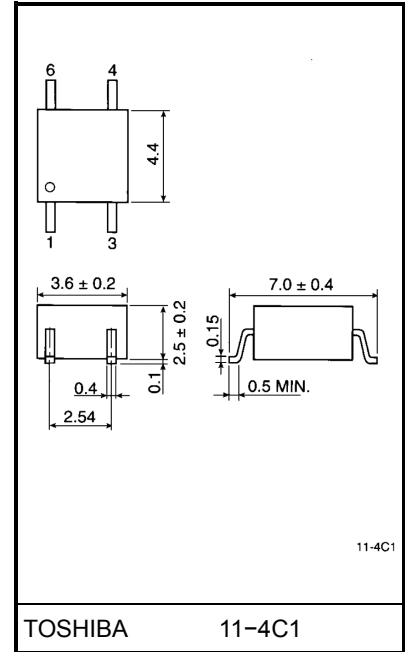
# TLP181

Office Machine  
 Programmable Controllers  
 AC / DC Input Module  
 Telecommunication

The TOSHIBA mini flat coupler TLP□8□ is a small outline coupler, suitable for surface mount assembly. TLP□8□ consist of a photo transistor optically coupled to a gallium arsenide infrared emitting diode.

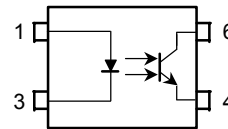
- Collector-emitter voltage: 80V (min.)
- Current transfer ratio: 50% (min.)  
 Rank GB: □00% (min.)
- Isolation voltage: 3750Vrms (min.)
- UL recognized: UL□577,  
 file no. E67349
- Option (V4) type  
 VDE approved: VDE0884 satisfied  
 Maximum operating insulation voltage: 565V<sub>PK</sub>  
 Highest permissible over voltage: 6000V<sub>PK</sub>

Unit in mm



Weight: 0.09 g

## Pin Configuration (top view)



- 1: Anode
- 3: Cathode
- 4: Emitter
- 6: Collector

## Current Transfer Ratio

Type	Classification *1	Current Transfer Ratio (%) ( $I_C / I_F$ )		Marking Of Classification
		$I_F = 5\text{mA}, V_{CE} = 5\text{V}, T_a = 25^\circ\text{C}$		
		Min.	Max.	
TLP181	(None)	50	600	BLANK, Y, Y <sup>■</sup> , G, G <sup>■</sup> , B, B <sup>■</sup> , GB
	Rank Y	50	150	Y, Y <sup>■</sup>
	Rank GR	100	300	G, G <sup>■</sup>
	Rank BL	200	600	B, B <sup>■</sup>
	Rank GB	100	600	G, G <sup>■</sup> , B, B <sup>■</sup> , GB

\*1: EX, Rank GB: TLP181 (GB)

(Note) Application, type name for certification test, please use standard product type name, i. e.  
TLP181 (GB): TLP181

## Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
LED	Forward current	$I_F$	50	mA
	Forward current derating	$\Delta I_F / ^\circ\text{C}$	-0.7 (Ta $\geq$ 53°C)	mA / °C
	Pulse forward current (100µs pulse, 100pps)	$I_{FP}$	1	A
	Reverse voltage	$V_R$	5	V
	Junction temperature	$T_j$	125	°C
Detector	Collector-emitter voltage	$V_{CEO}$	80	V
	Emitter-collector voltage	$V_{ECO}$	7	V
	Collector current	$I_C$	50	mA
	Collector power dissipation (1 Circuit)	$P_C$	150	mW
	Collector power dissipation derating (1 Circuit Ta $\geq$ 25°C)	$\Delta P_C / ^\circ\text{C}$	-1.5	mW / °C
	Junction temperature	$T_j$	125	°C
Storage temperature range		$T_{stg}$	-55~125	°C
Operating temperature range		$T_{opr}$	-55~100	°C
Lead soldering temperature		$T_{sol}$	260 (10s)	°C
Total package power dissipation		$P_T$	200	mW
Total package power dissipation derating (Ta $\geq$ 25°C)		$\Delta P_T / ^\circ\text{C}$	-2.0	mW / °C
Isolation voltage (AC, 1min., R.H. $\leq$ 60%) (Note 1)		$BV_S$	3750	$V_{rms}$

(Note 1) Device considered a two-terminal device: Pin1, 3 shorted together and pins 4, 6 shorted together

## Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	$V_{CC}$	—	5	48	V
Forward current	$I_F$	—	16	20	mA
Collector current	$I_C$	—	1	10	mA
Operating temperature	$T_{opr}$	-25	—	85	°C

## Individual Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	$V_F$	$I_F = 10 \text{ mA}$	1.0	1.15	1.3	V
	Reverse current	$I_R$	$V_R = 5 \text{ V}$	—	—	10	$\mu\text{A}$
	Capacitance	$C_T$	$V = 0, f = 1 \text{ MHz}$	—	30	—	pF
Detector	Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 0.5 \text{ mA}$	80	—	—	V
	Emitter-collector breakdown voltage	$V_{(BR)ECO}$	$I_E = 0.1 \text{ mA}$	7	—	—	V
	Collector dark current	$I_{CEO}$	$V_{CE} = 48 \text{ V}, (\text{ Ambient light below } 1000 \text{ lx})$	—	0.01 (2)	0.1 (10)	$\mu\text{A}$
			$V_{CE} = 48 \text{ V}, T_a = 85^\circ\text{C}, (\text{ Ambient light below } 1000 \text{ lx})$	—	2 (4)	50 (50)	$\mu\text{A}$
Capacitance (collector to emitter)	$C_{CE}$	$V = 0, f = 1 \text{ MHz}$	—	10	—	pF	

## Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Current transfer ratio	$I_C / I_F$	$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_F (\text{sat})$	$I_F = 1 \text{ mA}, V_{CE} = 0.4 \text{ V}$ Rank GB	—	60	—	%
			30	—	—	
Collector-emitter saturation voltage	$V_{CE} (\text{sat})$	$I_C = 2.4 \text{ mA}, I_F = 8 \text{ mA}$	—	—	0.4	V
		$I_C = 0.2 \text{ mA}, I_F = 1 \text{ mA}$ Rank GB	—	0.2	—	
Off-state collector current	$I_C (\text{off})$	$V_F = 0.7 \text{ V}, V_{CE} = 48 \text{ V}$	—	1	10	$\mu\text{A}$

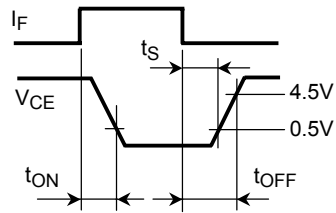
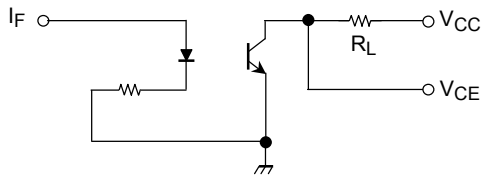
## Isolation Characteristics (Ta = 25°C)

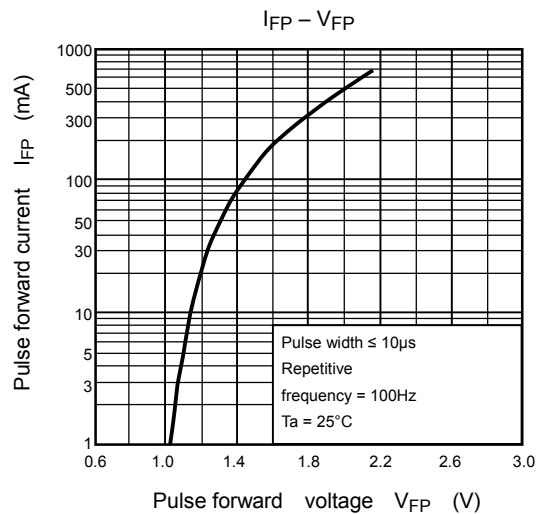
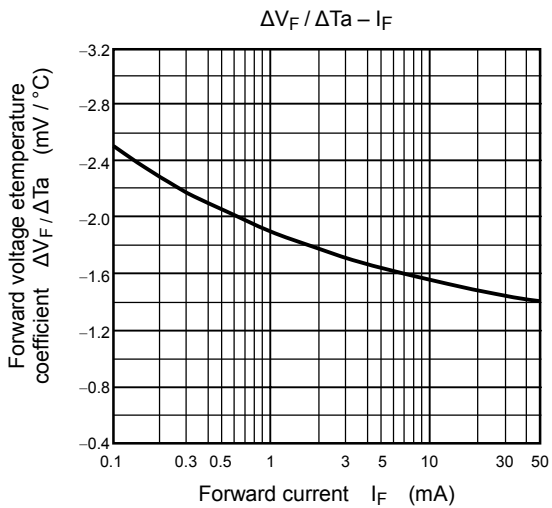
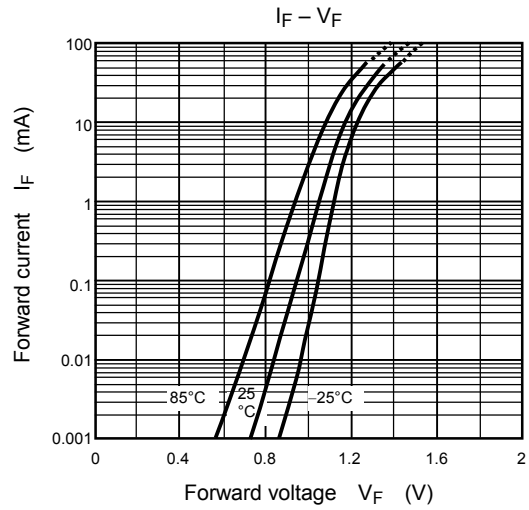
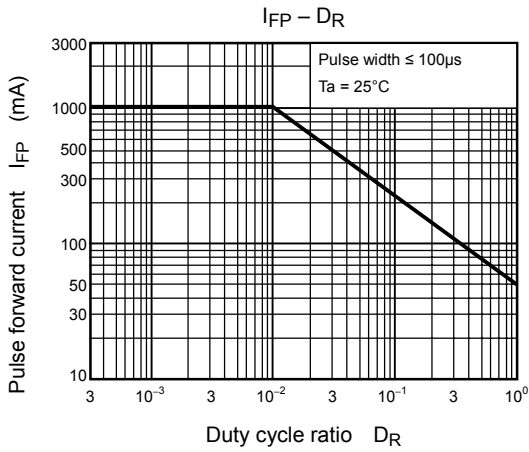
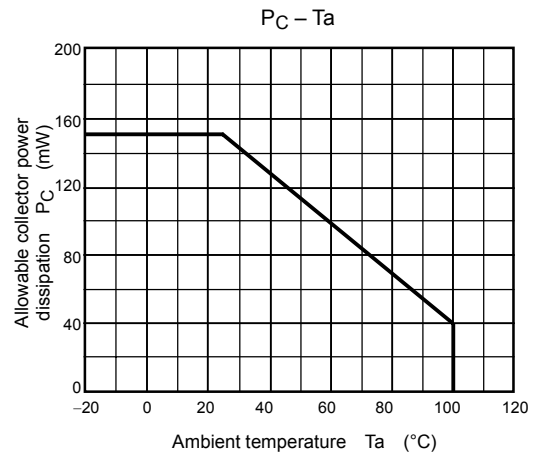
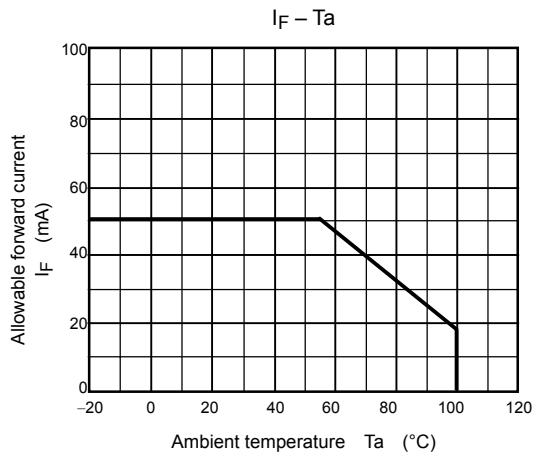
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Capacitance (input to output)	$C_S$	$V_S = 0 \text{ V}, f = 1 \text{ MHz}$	—	0.8	—	pF
Isolation resistance	$R_S$	$V_S = 500 \text{ V}, \text{ R.H.} \leq 60\%$	$1 \times 10^{12}$	$10^{14}$	—	$\Omega$
Isolation voltage	$BV_S$	AC, 1 minute	3750	—	—	$V_{\text{rms}}$
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	$V_{\text{dc}}$

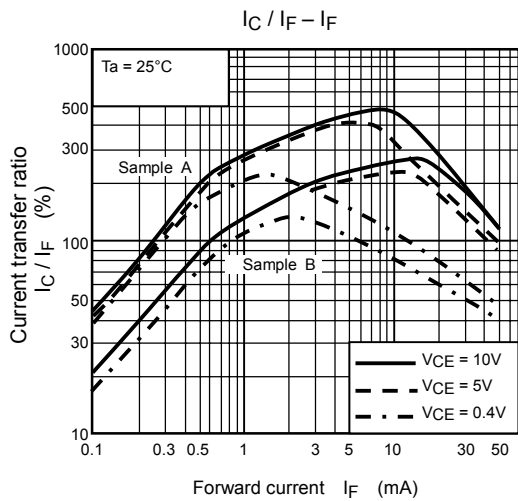
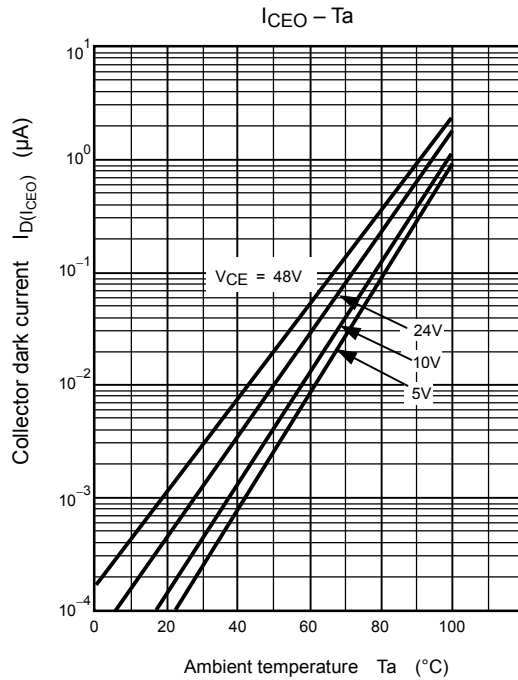
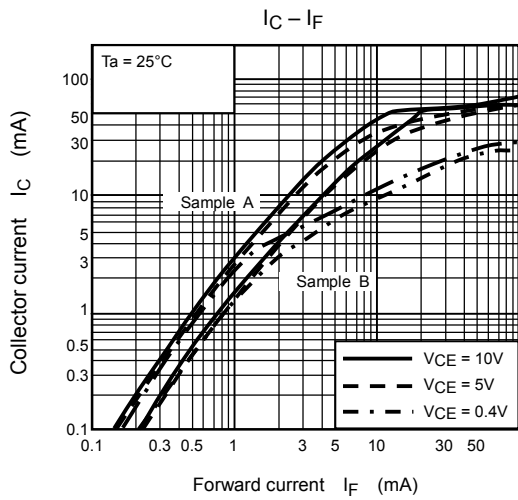
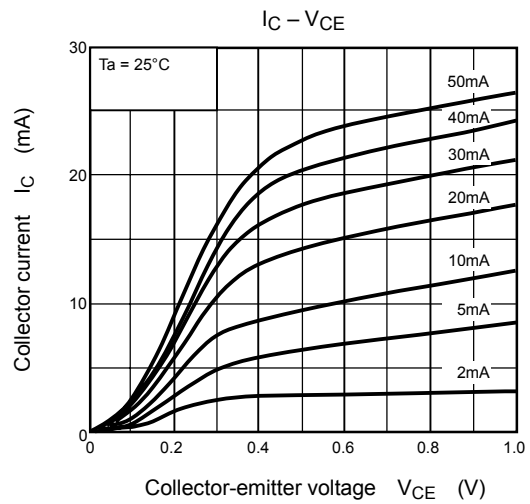
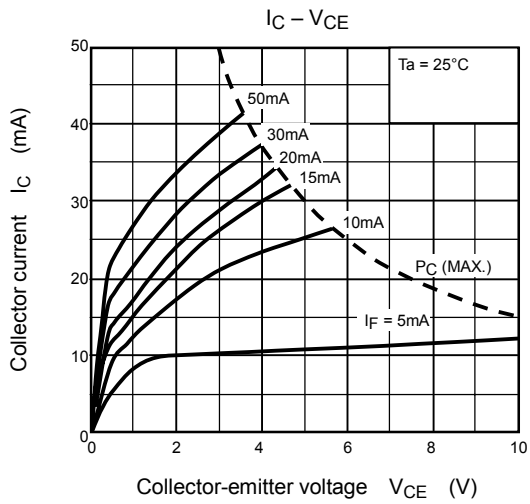
**Switching Characteristics (Ta = 25°C)**

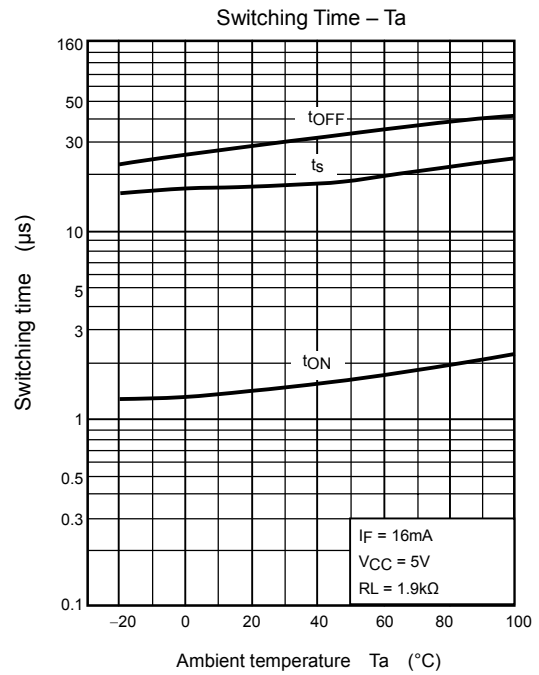
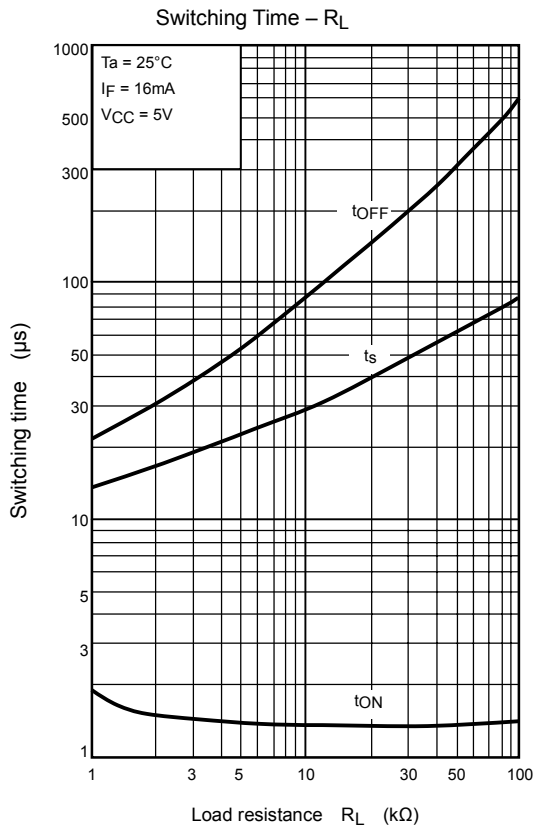
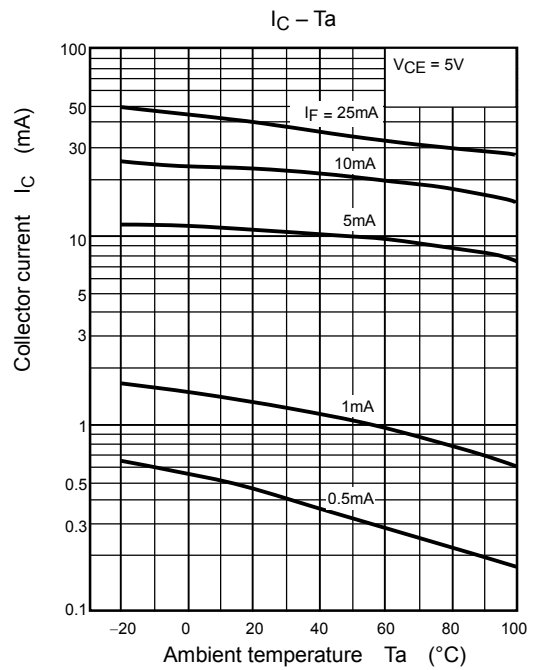
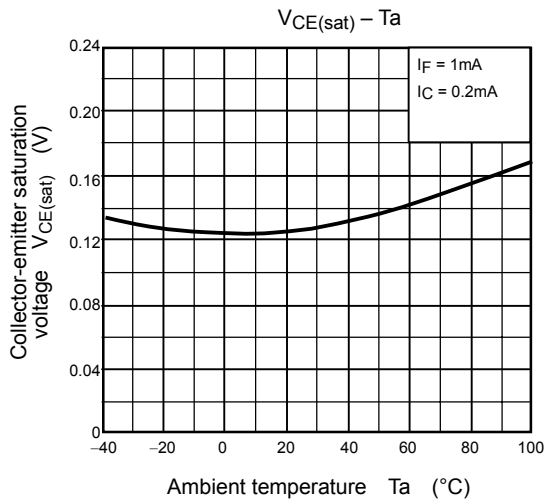
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Rise time	$t_r$	$V_{CC} = 10\text{ V}, I_C = 2\text{ mA}$ $R_L = 100\Omega$	—	2	—	$\mu\text{s}$
Fall time	$t_f$		—	3	—	
Turn-on time	$t_{on}$		—	3	—	
Turn-off time	$t_{off}$		—	3	—	
Turn-on time	$t_{ON}$	$R_L = 1.9\text{ k}\Omega$ $V_{CC} = 5\text{ V}, I_F = 16\text{ mA}$ (Fig.1)	—	2	—	$\mu\text{s}$
Storage time	$t_s$		—	25	—	
Turn-off time	$t_{OFF}$		—	40	—	

Fig. 1 Switching time test circuit











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